INFORMATION DISCLOSURE STATEMENT	Case Name.	J.W. Hsu 4-5
	Serial No.	J.W. Hsy, et al.
	Applicant:	*10/735 191*
	Filing Date:	December 12, 2003
	Group:	

U.S. PATENT DOCUMENTS

*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Dat
JN	AA	6,086,673	July 11, 2000	Richard J. Molnar	117	90	April 2, 1998
JN	AB	2002/0086534	7/4/02	Cuomo et al.	438	689	11/30/01

FOREIGN PATENT DOCUMENTS

		Document Number	Date	Country	Class	Subclass	Translation

OTHER (including Author, Title, Date, Pertinent Pages, etc.)

JN	AC	E.J. Miller et al., "Reduction of reverse-bias leakage current in Schottky diodes on GaN grown by molecular-beam epitaxy using surface modification with an atomic force microscope", Journal of Applied Physics, Vol. 91, No. 12, June 15, 2002, pages 9821-9826.
	AD	E.J. Miller et al., "Reverse-bias leakage current reduction in GaN Schottky diodes by surface modification with an atomic force microscope," Abstract from Technical Program Session V of Electronic Materials Conference, Santa Barbara, CA (June 25-27, 2002) 1 page (Note: may have been published before June 25, 2002).
	AE	E.J. Miller et al., "CHARACTERIZATION AND LOCAL PASSIVATION OF REVERSE-BIAS CURRENT LEAKAGE PATHS IN AN AlGaN/GaN HETEROSTRUCTURE, Abstract from Nov. 2001 MRS Fall Meeting," Symposium 1, Session I 10.7 (1 page), publ.'d online at www. mrs.org/meetings/fall 2001.
	AF	Lee, J.J., et al., "MBE Growth of Wurtzite GaN on LaA1O$_3$ (100) Substrate," Journal of Crystal Growth, Vol. 213, No. 1-2, pp. 33-39, May 2000.

***References listed beyond AZ would list as AA-1, AB-2, AC-3 thru AZ-26.
***Note First Page ONLY Header/Footer. Subsequent pages must ONLY have <u>page # layout</u> as header

EXAMINER	DATE CONSIDERED
JOSEPH NGUYEN	10/10/04

*Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609: Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant

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